

L Number	Hits	Search Text	DB	Time stamp
-	81	oxide and (particle near3 beam) and (semiconductor or crystal) and silicon and cobalt	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 15:07
-	15	oxide same (particle near3 beam) and (semiconductor or crystal) and silicon and cobalt	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 15:08
-	66	(particle near3 beam) and silicon and (oxygen near3 (content or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 15:40
-	5	(particle near3 beam) same (oxygen near3 (content or concentration)) and silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 15:39
-	10	(particle near3 beam) same oxide and silicon and (oxygen near3 (content or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 16:17
-	54	(particle near3 beam) and oxide and silicon and (oxygen near3 (content or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 16:33
-	4	colbalt near3 silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 16:33
-	19	(cobalt near3 silicide) and beam and oxide and (oxygen near3 (content or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 16:57
-	66	(cobalt near3 silicide) and (oxygen near3 (content or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 16:58
-	13	(cobalt near3 silicide) same (oxygen near3 (content or concentration))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 17:00
-	52	(cobalt near3 silicide) and (oxygen near3 (content or concentration)) same (silicon or substrate or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 17:08
-	102	(silicon near2 (oxide or dioxide)) same beam same oxygen and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 17:09
-	63	(silicon near2 (oxide or dioxide)) same beam same oxygen and silicide and @py<2001	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/30 17:10

-	4	(anneal\$3 or rta or rtp or (rapid adj thermal) or (heat adj treat\$4) or ptp) and cobalt near3 silicide and oxide and (particle near3 beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 10:00
-	168	(anneal\$3 or rta or rtp or (rapid adj thermal) or (heat adj treat\$4) or ptp) and cobalt near3 silicide and oxide and (silicon near3 (substrate or wafer or surface)) and beam	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 11:33
-	119	oxide and silicon and beam same crystallinity and silicide	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 11:35
-	17	silicon and beam same crystallinity same oxide and silicide	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 11:43
-	92	silicon and beam same oxide same improv\$5 and silicide	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 13:37
-	296	silicon and beam same oxide same remov\$5 and silicide	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/07/31 13:39